## **Complementary Silicon Power Transistors**

The MJ15003 and MJ15004 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications.

- High Safe Operating Area (100% Tested) 250 W @ 50 V
- For Low Distortion Complementary Designs
- High DC Current Gain —

hFF = 25 (Min) @ IC = 5 Adc

# MJ15003\* MJ15004\*

\*Motorola Preferred Device

20 AMPERE **POWER TRANSISTORS COMPLEMENTARY** SILICON **140 VOLTS 250 WATTS** 



TO-204AA (TO-3)

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	140	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	140	Vdc
Emitter–Base Voltage	V <sub>EBO</sub>	5	Vdc
Collector Current — Continuous	IC	20	Adc
Base Current — Continuous	IВ	5	Adc
Emitter Current — Continuous	ΙΕ	25	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	250 1.43	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	0.70	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/16" from Case for ≤ 10 seconds	TL	265	°C

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7



#### \*ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	
Collector Emitter Sustaining Voltage (1) (IC = 200 mAdc, I <sub>B</sub> = 0)	VCEO(sus)	140	_	Vdc
Collector Cutoff Current (VCE = 140 Vdc, VBE(off) = 1.5 Vdc) (VCE = 140 Vdc, VBE(off) = 1.5 Vdc, T <sub>C</sub> = 150°C)	ICEX	_	100 2	μAdc mAdc
Collector Cutoff Current (VCE = 140 Vdc, I <sub>B</sub> = 0)	ICEO	_	250	μAdc
Emitter Cutoff Current (VEB = 5 Vdc, IC = 0)	l <sub>EBO</sub>	_	100	μAdc
SECOND BREAKDOWN			•	
Second Breakdown Collector Current with Base Forward Baised (VCE = 50 Vdc, t = 1 s (non repetitive)) (VCE = 100 Vdc, t = 1 s (non repetitive))	I <sub>S/b</sub>	5 1		Adc
ON CHARACTERISTICS	<u> </u>			
DC Current Gain (IC = 5 Adc, VCE = 2 Vdc)	hFE	25	150	
Collector Emitter Saturation Voltage (I <sub>C</sub> = 5 Adc, I <sub>B</sub> = 0.5 Adc)	VCE(sat)	_	1	Vdc
Base Emitter On Voltage (I <sub>C</sub> = 5 Adc, V <sub>CE</sub> = 2 Vdc)	V <sub>BE</sub> (on)	_	2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product ( $I_C = 0.5$ Adc, $V_{CE} = 10$ Vdc, $f_{test} = 0.5$ MHz)	fT	2	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	c <sub>ob</sub>	_	1000	pF

<sup>(1)</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2%.

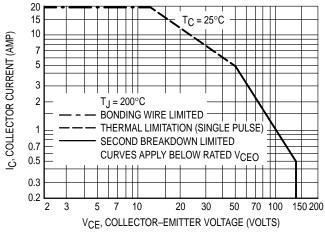
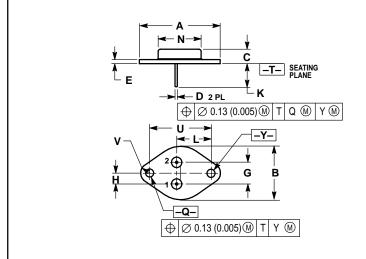


Figure 1. Active-Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 200^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

### **PACKAGE DIMENSIONS**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В	-	1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Η	0.215	BSC	5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665	BSC	16.89 BSC		
N		0.830		21.08	
ø	0.151	0.165	3.84	4.19	
5	1.187 BSC		30.15 BSC		
V	0.131	0.188	3 33	4 77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

**CASE 1-07** TO-204AA (TO-3) ISSUE Z

#### MJ15003 MJ15004

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